TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSV)

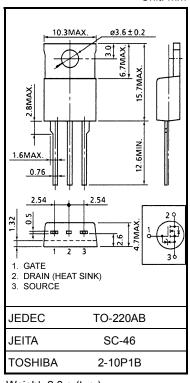
2SK2841

Chopper Regulator, DC–DC Converter and Motor Drive Applications

- Low drain-source ON resistance $: RDS (ON) = 0.4 \Omega (typ.)$
- High forward transfer admittance $|Y_{fs}| = 8.0 \text{ S} (typ.)$
- Low leakage current $: IDSS = 100 \mu A (max) (VDS = 400 V)$
- Enhancement mode : $V_{th} = 2.0 \sim 4.0 V (V_{DS} = 10 V, I_D = 1 mA)$

Maximum Ratings (Ta = 25°C)

Characteri	stics	Symbol	Rating	Unit	
Drain-source voltage		V _{DSS}	400	V	
Drain-gate voltage (R _{GS} = 20 kΩ)		V _{DGR}	400	V	
Gate-source voltage		V _{GSS}	±30	V	
Drain current	DC (Note 1)	I _D	10	А	
	Pulse (Note 1)	I _{DP}	40	А	
Drain power dissipatio	n (Tc = 25°C)	PD	80	W	
Single pulse avalanche energy (Note 2)		E _{AS}	360	mJ	
Avalanche current		I _{AR}	10	A	
Repetitive avalanche energy (Note 3)		E _{AR}	8	mJ	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	



Weight: 2.0 g (typ.)

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch-c)}	1.56	°C / W
Thermal resistance, channel to ambient	R _{th (ch−a)}	83.3	°C / W

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 5.85 mH, R_G = 25 Ω , I_{AR} = 10 A

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Please handle with caution.

Unit: mm

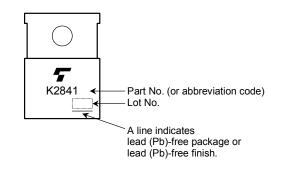
Electrical Characteristics (Ta = 25°C)

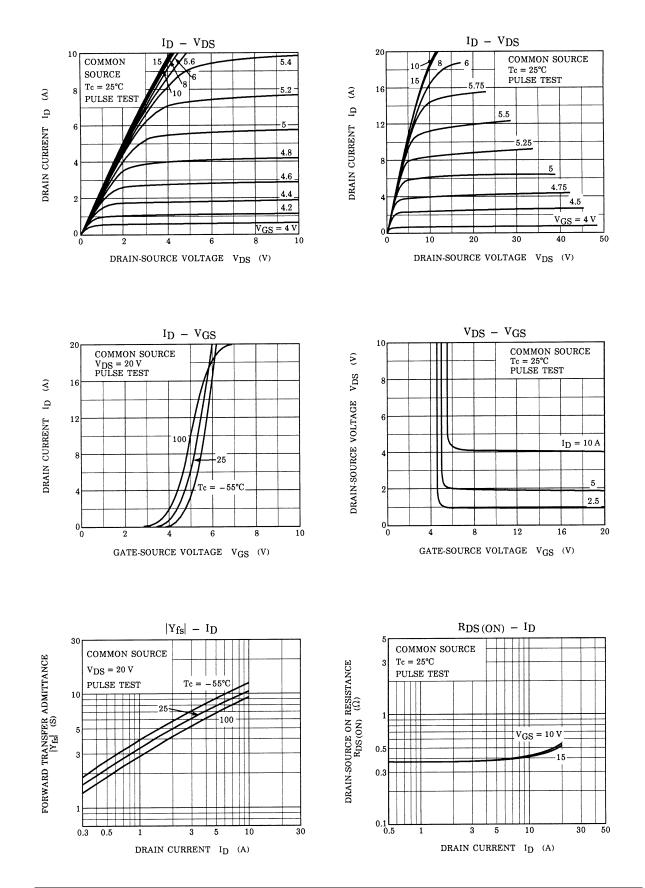
Chara	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	V _{GS} = ±25 V, V _{DS} = 0 V			±10	μA
Gate-source br	eakdown voltage	V (BR) GSS	I _G = ±10 μA, V _{DS} = 0 V		_		V
Drain cut-off cu	irrent	I _{DSS}	V _{DS} = 400 V, V _{GS} = 0 V		_	100	μA
Drain-source b	reakdown voltage	V (BR) DSS	I _D = 10 mA, V _{GS} = 0 V	400	_	_	V
Gate threshold	voltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	2.0	_	4.0	V
Drain-source O	N resistance	R _{DS (ON)}	V _{GS} = 10 V, I _D = 5.0 A	_	0.4	0.55	Ω
Forward transfe	r admittance	Y _{fs}	V _{DS} = 10 V, I _D = 5.0 A	4.0	8.0	_	S
Input capacitance Reverse transfer capacitance		C _{iss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	_	1340	_	pF
		C _{rss}		_	160	_	
Output capacitance		C _{oss}			490	_	
Switching time	Rise time	tr	$V_{GS} \stackrel{10V}{}_{0V} \stackrel{I_{D}=5.0A}{}_{VOUT} V_{OUT} R_{L} = 40\Omega$ $V_{DD} = 200V$ $Duty \leq 1\%, t_{W} = 10\mu s$		22	_	ns
	Turn-on time	t _{on}			60	_	
	Fall time	t _f		_	32	_	
	Turn-off time	t _{off}		_	140	_	
Total gate charge (gate-source plus gate-drain)		Qg		_	34	_	
Gate-source charge		Q _{gs}	V _{DD} ≈ 320 V, V _{GS} = 10 V, I _D = 10 A		18	_	nC
Gate-drain ("miller") Charge		Q _{gd}			16	_	

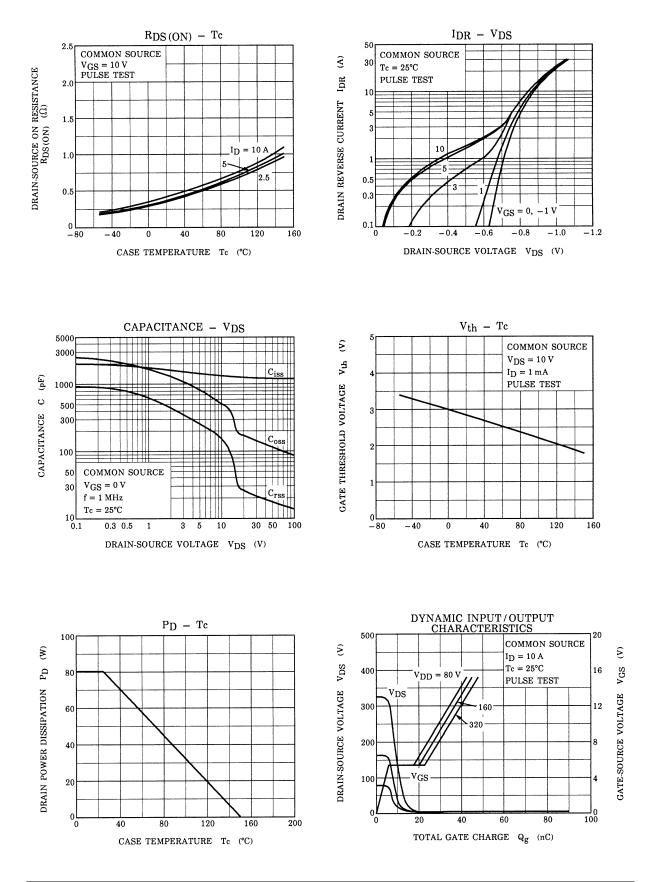
Source–Drain Ratings and Characteristics (Ta = 25°C)

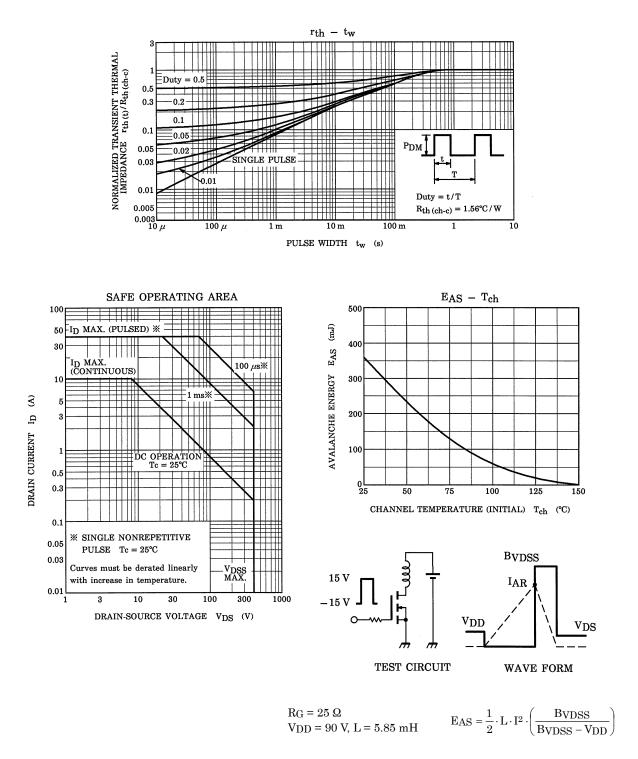
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	—	_	_	10	А
Pulse drain reverse current (Note 1)	I _{DRP}	_	-	_	40	А
Forward voltage (diode)	V _{DSF}	I _{DR} = 10 A, V _{GS} = 0 V	_	—	-1.7	V
Reverse recovery time	t _{rr}	I _{DR} = 10 A, V _{GS} = 0 V dI _{DR} / dt = 100 A / μs		350		ns
Reverse recovery charge	Q _{rr}	dI _{DR} / dt = 100 A / μs		2.6	1	μC

Marking









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